

Features

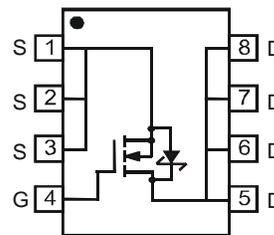
- DIOFET utilizes a unique patented process to monolithically integrate a MOSFET and a Schottky in a single die to deliver:
 - Low $R_{DS(ON)}$ - minimizes conduction losses
 - Low V_{SD} - reducing the losses due to body diode conduction
 - Low Q_{rr} - lower Q_{rr} of the integrated Schottky reduces body diode switching losses
 - Low gate capacitance (Q_g/Q_{gs}) ratio – reduces risk of shoot-through or cross conduction currents at high frequencies
 - Avalanche rugged – I_{AR} and E_{AR} rated
- Lead Free, RoHS Compliant (Note 1)**
- "Green" Device (Note 2)**
- Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.072 grams (approximate)



Top View


 Top View
Internal Schematic

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

| Characteristic | Symbol | Value | Unit |
|--|-----------|--|------|
| Drain-Source Voltage | V_{DSS} | 30 | V |
| Gate-Source Voltage | V_{GSS} | ± 12 | V |
| Continuous Drain Current (Note 3) $V_{GS} = 4.5\text{V}$ | I_D | $T_A = 25^\circ\text{C}$ $T_A = 85^\circ\text{C}$ | A |
| | | 9.8 6.3 | |
| Pulsed Drain Current (Note 4) | I_{DM} | 90 | A |
| Avalanche Current (Note 4) (Note 5) | I_{AR} | 13 | A |
| Repetitive Avalanche Energy (Note 4) (Note 5) $L = 0.3\text{mH}$ | E_{AR} | 25.4 | mJ |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|---|-----------------|-------------|--------------------|
| Power Dissipation (Note 3) | P_D | 1.54 | W |
| Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ\text{C}$ (Note 3) | $R_{\theta JA}$ | 81 | $^\circ\text{C/W}$ |
| Operating and Storage Temperature Range | T_J, T_{STG} | -55 to +150 | $^\circ\text{C}$ |

- Notes:
- No purposefully added lead.
 - Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 - Device mounted on minimum recommended layout. The value in any given application depends on the user's specific board design.
 - Repetitive rating, pulse width limited by junction temperature.
 - I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep $T_J = 25^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise stated

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|--|--------------|------|-------|-----------|-----------|--|
| OFF CHARACTERISTICS (Note 6) | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | 30 | - | - | V | $V_{GS} = 0V, I_D = 250\mu A$ |
| Zero Gate Voltage Drain Current | I_{DSS} | - | - | 0.1 | mA | $V_{DS} = 30V, V_{GS} = 0V$ |
| Gate-Source Leakage | I_{GSS} | - | - | ± 100 | nA | $V_{GS} = \pm 12V, V_{DS} = 0V$ |
| ON CHARACTERISTICS (Note 6) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | 1.0 | - | 2.3 | V | $V_{DS} = V_{GS}, I_D = 250\mu A$ |
| Static Drain-Source On-Resistance | $R_{DS(on)}$ | - | 9 | 13 | $m\Omega$ | $V_{GS} = 10V, I_D = 9.8A$ |
| | | - | 11 | 16 | | $V_{GS} = 4.5V, I_D = 9.8A$ |
| Forward Transfer Admittance | $ Y_{fs} $ | - | 5 | - | S | $V_{DS} = 5V, I_D = 9.8A$ |
| Diode Forward Voltage | V_{SD} | - | 0.4 | 1 | V | $V_{GS} = 0V, I_S = 1A$ |
| Maximum Body-Diode + Schottky Continuous Current | I_S | - | - | 5 | A | - |
| DYNAMIC CHARACTERISTICS (Note 7) | | | | | | |
| Input Capacitance | C_{iss} | - | 1849 | - | pF | $V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz$ |
| Output Capacitance | C_{oss} | - | 158 | - | pF | |
| Reverse Transfer Capacitance | C_{rss} | - | 123 | - | pF | |
| Gate Resistance | R_g | 0.53 | 2.68 | 4.82 | Ω | $V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$ |
| Total Gate Charge $V_{GS} = 4.5V$ | Q_g | - | 18.5 | - | nC | $V_{DS} = 15V, V_{GS} = 10V, I_D = 9.8A$ |
| Total Gate Charge $V_{GS} = 10V$ | Q_g | - | 43 | - | nC | |
| Gate-Source Charge | Q_{gs} | - | 4.7 | - | nC | |
| Gate-Drain Charge | Q_{gd} | - | 4.0 | - | nC | |
| Turn-On Delay Time | $t_{D(on)}$ | - | 6.62 | - | ns | $V_{GS} = 10V, V_{DS} = 10V, R_G = 3\Omega, R_L = 1.2\Omega$ |
| Turn-On Rise Time | t_r | - | 8.73 | - | ns | |
| Turn-Off Delay Time | $t_{D(off)}$ | - | 36.41 | - | ns | |
| Turn-Off Fall Time | t_f | - | 4.69 | - | ns | |

- Notes:
6. Short duration pulse test used to minimize self-heating effect.
 7. Guaranteed by design. Not subject to production testing.

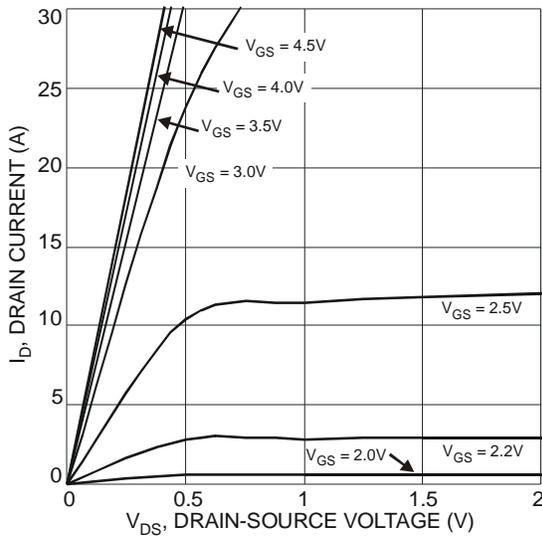


Fig. 1 Typical Output Characteristic

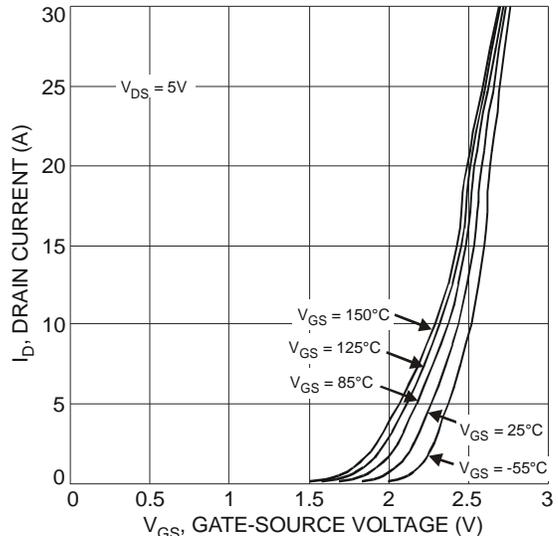


Fig. 2 Typical Transfer Characteristic

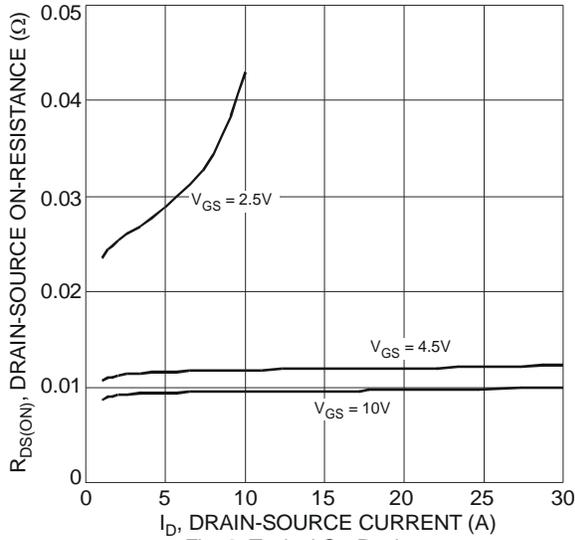


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

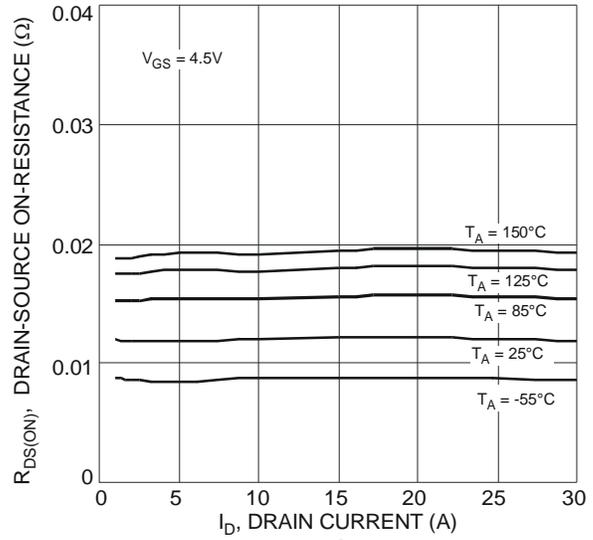


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

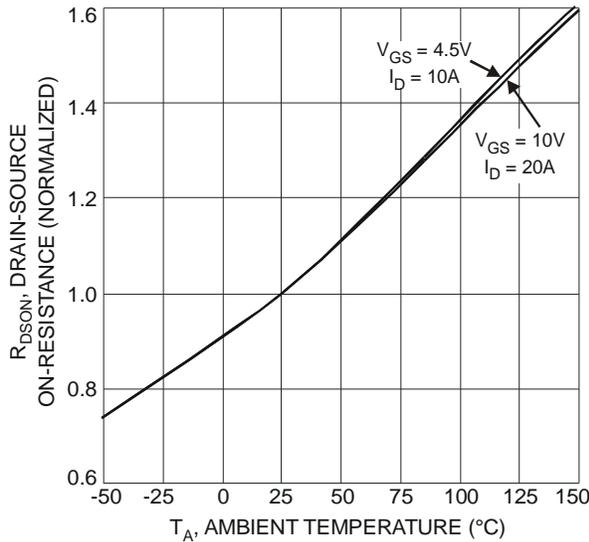


Fig. 5 On-Resistance Variation with Temperature

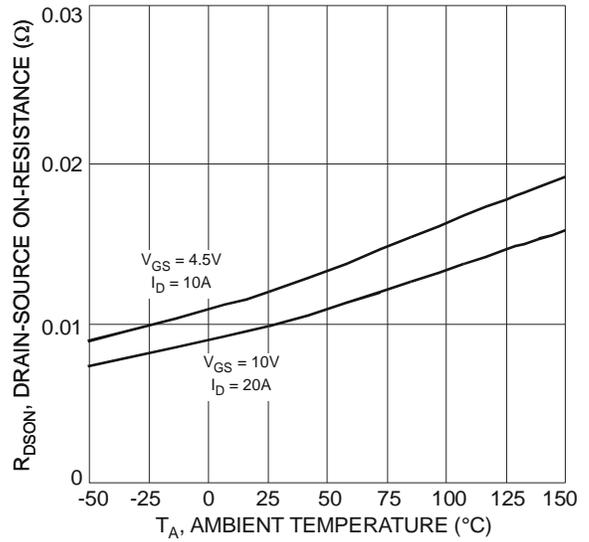


Fig. 6 On-Resistance Variation with Temperature

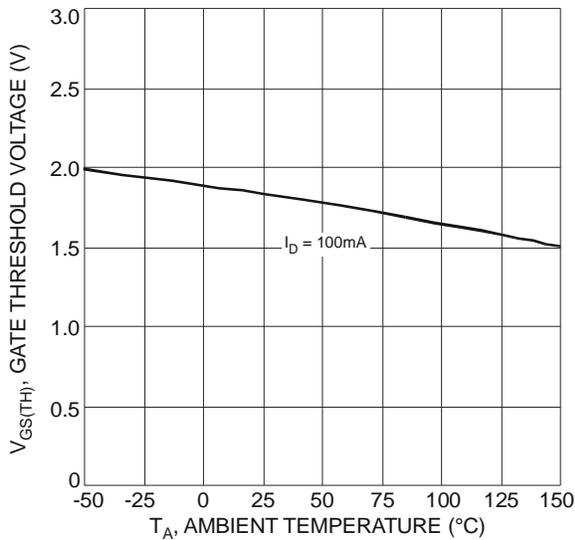


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

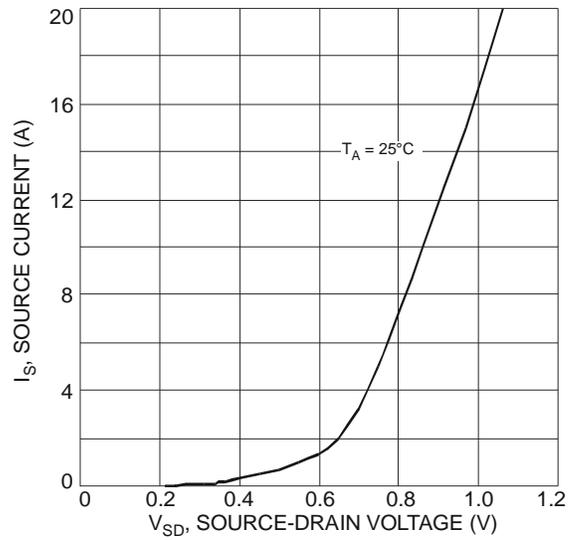
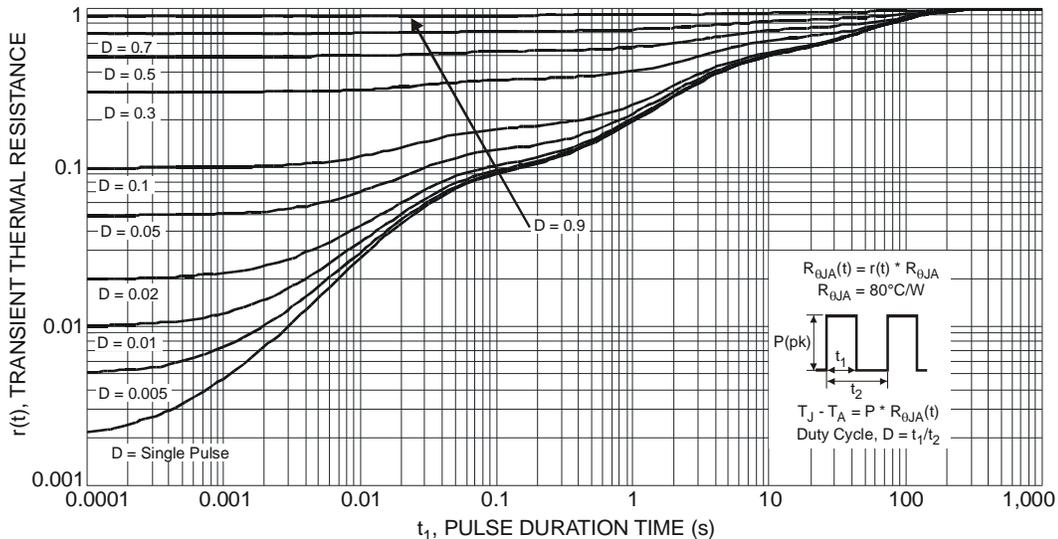
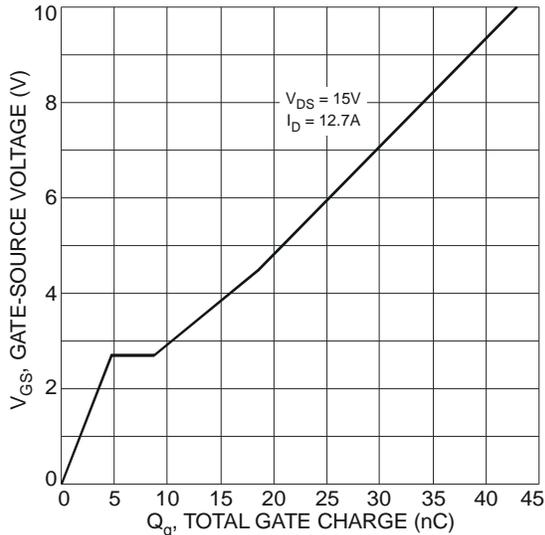
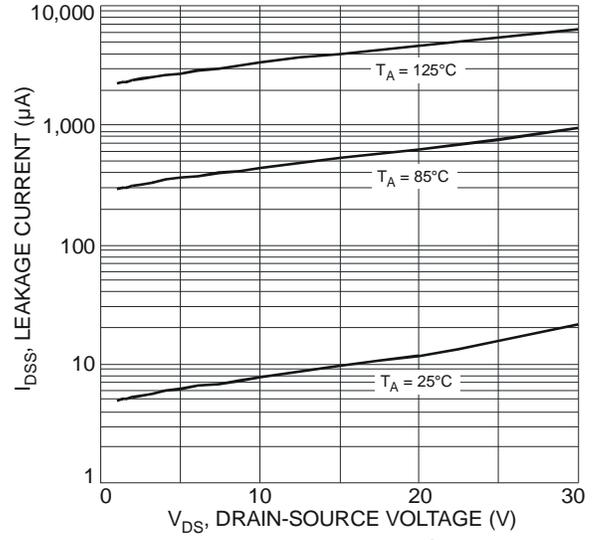
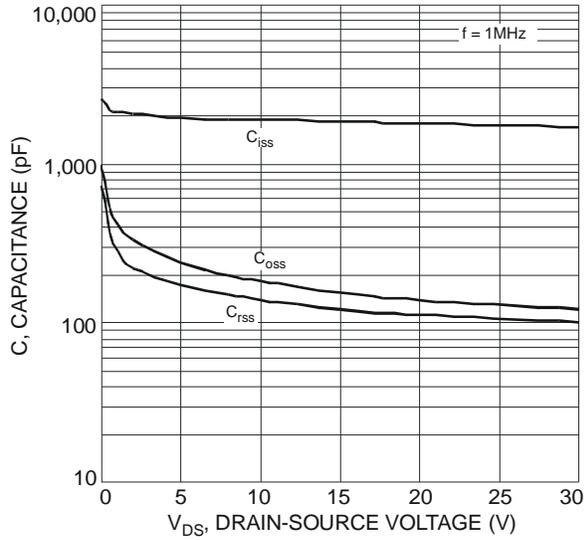


Fig. 8 Diode Forward Voltage vs. Current



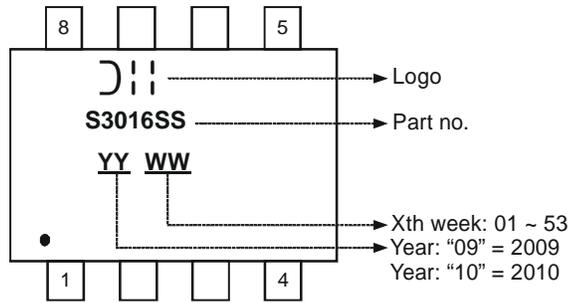
NEW PRODUCT

Ordering Information (Note 8)

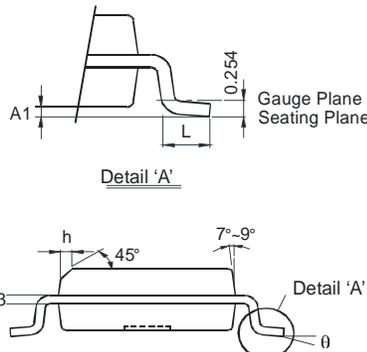
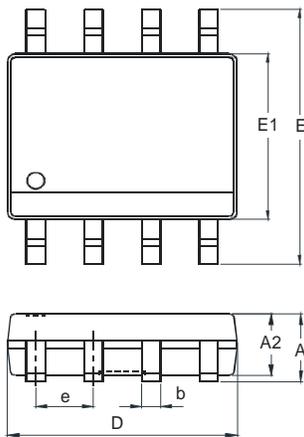
| Part Number | Case | Packaging |
|---------------|------|--------------------|
| DMS3016SSS-13 | SO-8 | 2500 / Tape & Reel |

Notes: 8. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information

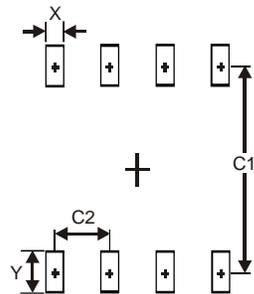


Package Outline Dimensions



| SO-8 | | |
|----------------------|----------|------|
| Dim | Min | Max |
| A | - | 1.75 |
| A1 | 0.10 | 0.20 |
| A2 | 1.30 | 1.50 |
| A3 | 0.15 | 0.25 |
| b | 0.3 | 0.5 |
| D | 4.85 | 4.95 |
| E | 5.90 | 6.10 |
| E1 | 3.85 | 3.95 |
| e | 1.27 Typ | |
| h | - | 0.35 |
| L | 0.62 | 0.82 |
| θ | 0° | 8° |
| All Dimensions in mm | | |

Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| X | 0.60 |
| Y | 1.55 |
| C1 | 5.4 |
| C2 | 1.27 |

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